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an active layer provided between the second and third semiconductor layers, the active layer emitting light with charge injected therein from the second and third semiconductor layers; and

a graded composition layer provided between the active layer and the third semiconductor layer to have a varying composition,

wherein the composition of the graded composition layer is equal to a composition of the third semiconductor layer at an interface with the third semiconductor layer, and to a composition of the active layer at an interface with the active layer,

wherein a base electrode is electrically connected to the third semiconductor layer via the graded composition layer and the active layer, and

wherein the forbidden band of the active layer is smaller than the forbidden band of the third semiconductor layer.

C2  
15. (Amended) The semiconductor light-emitting device of claim 1, wherein regions of the active layer and the graded composition layer lying between the base electrode and the second semiconductor layer are removed.

C3  
20 (Amended) The semiconductor light-emitting device of claim 1, wherein the third semiconductor layer is p-type.